

INCHANGE SEMICONDUCTOR

isc Silicon NPN Power Transistor

BUR22

DESCRIPTION

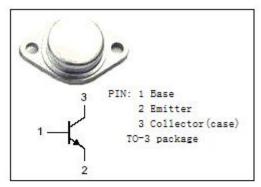
- Low Collector Saturation Voltage-
- : V_{CE(sat)}= 1.0V (Max.) @I_C= 20A
- High Switching Speed
- · High DC Current Gain-
- : h_{FE}= 10(Min.) @I_C= 20A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

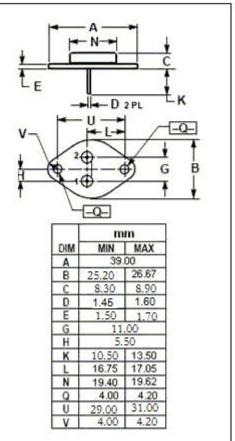
APPLICATIONS

• Designed for high current, high speed, high power applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	v	ALUE	UNIT					
V _{CBO}	Collector-Base Voltage		350	V					
VCEO	Collector-Emitter Voltage		250	V					
VEBO	Emitter-Base Voltage		7	V					
Ic	Collector Current-Continuous		40	А					
I _{CM}	Collector Current-Peak		50	А					
I _B	Base Current-Continuous	8		А					
Pc	Collector Power Dissipation @Tc=25℃	250		W					
Tj	Junction Temperature	200		°C					
T _{stg}	Storage Temperature Range	-65~200		°C					
THERMAL CHARACTERISTICS									
SYMBOL	PARAMETER		MAX	UNIT					
Rth j-c	Thermal Resistance,Junction to Case	9	0.7	℃ /W					







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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\!^{\circ}_{\circ}$ unless otherwise specified

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V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 50mA; I _B = 0	250		V
V(BR)EBO	Emitter-Base Breakdown Voltage	I _E = 1mA; I _C = 0	7		V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 20A; I _B =2A		1.0	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 40A ;I _B = 10A		3.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 20A; I _B =2A		2.0	V
I _{CEO}	Collector Cutoff Current	V _{CE} = 250V; I _B = 0		0.5	mA
I _{CBO}	Collector Cutoff Current	V _{CB} = 350V; I _C =0		0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0		0.1	mA
h _{FE-1}	DC Current Gain	I _C = 1A ; V _{CE} = 4V	60	200	
h _{FE-2}	DC Current Gain	I _C = 10A ; V _{CE} = 4V	20		
h _{FE-3}	DC Current Gain	I _C = 20A ; V _{CE} = 4V	10		
f _T	Current-Gain—Bandwidth Product	I _C = 0.5A;V _{CE} = 10V, f _{test} = 1MHz	10		MHz

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